PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants

Pietro Erratico et al.

Filed

: November 12, 2003

For

PROCESS FOR FORMING A BURIED CAVITY IN A

SEMICONDUCTOR MATERIAL WAFER AND A

BURIED CAVITY

Art Unit

: 1765

Docket No.

: 854063.618D1

Date

: November 12, 2003

Mail Stop Patent Application Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents:

In accordance with 37 C.F.R. §§ 1.56 and 1.97 through 1.98, applicants wish to make known to the Patent and Trademark Office the 17 references set forth on the attached Form PTO-1449. This application relies, under 35 U.S.C. § 120, on the earlier filing date of prior Application No. 09/797,206, filed February 27, 2001. The references listed on the attached Form PTO-1449 were submitted to and/or cited by the Patent and Trademark Office in this prior application and, therefore, are not required to be provided in this application. If the Examiner wishes, copies will be provided upon request. As to any reference supplied, applicants do not admit that it is "prior art" under 35 U.S.C. §§ 102 or 103, and specifically reserve the right to traverse or antedate any such reference, as by a showing under 37 C.F.R. § 1.131 or other method. Although the aforesaid references are made known to the Patent and Trademark Office in compliance with applicants' duty to disclose all information they are aware of which is believed relevant to the examination of the above-identified application, applicants believe that their invention is patentable.

Please acknowledge receipt of this Information Disclosure Statement and kindly make the cited references of record in the above-identified application.

Applicants believe this Information Disclosure Statement has been timely filed, however, the Director is authorized to charge any fee due by way of this Information Disclosure Statement to our Deposit Account No. 19-1090.

Respectfully submitted,

Seed Intellectual Property Law Group PLLC

Harold H. Bennett H

Registration No. 52,404

HHB:wt

Enclosures:

Postcard Form PTO-1449

701 Fifth Avenue, Suite 6300 Seattle, Washington 98104-7092

Phone: (206) 622-4900 Fax: (206) 682-6031

431482_1.DOC

									Sheet 1		
FORM PTO-1449 (REV.7-80))		I.S. DEPARTMENT ATENT AND TRAD	ATTY, DOCKET NO. APPLICATION NO. 854063.618D1							
INF	ORM.	ATION DISCLOSU	RE STATEM	ENT	APPLICANTS Pietro Erratico et al.						
		(Use several sheets if ne	cessary)	FILING DATE			GROL	JP ART UNIT			
			TIC	NA A CHORD BATTER :	November 12, 2003 PATENT DOCUMENTS						
*EXAMINER		DOCUMENT NUMBER	DATE DATE	PAIRNI	NAME CLASS SUBCLASS				FILING		
INITIAL	.,		07/13/76	Kuhn		156		17	IF APPRO	PRIATE	
	AA	3,969,168	02/19/91	Sidner		29		621.1			
	AB	4,993,143	06/30/98	Su et al.		257		531			
	AC	5,773,870		Diem et al.		438		52			
	AD	6,001,666	12/14/99								
AE 6,015,761 01/18/00 Merry et al. 438 727											
FOREIGN PATENT DOCUMENTS TRANSLATION											
		DOCUMENT NUMBER	DATE	COUNTRY					YES	NO	
	AF	JP62076783	04/08/87	Japan (Abstract Only)							
_	AG	JP62076784	84 04/08/87 Japan (Abstract Only)								
	АН	WO9417558	8 08/04/94 PCT						,		
	ΑĬ	0 658 927 A	06/21/95	Europe (+ Abstract)							
	AJ	960177-7 A	11/10/97	Sweden (+ Abstract)							
	AK	196 21 349 A	12/04/97	Germany (+ Abstract)							
	AL	1 043 770 A1	10/11/00	ĖP							
	AM	1 130 631 A1	09/05/01	ЕР							
OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)											
	Schubert, "Method of Making Separate Regions of Various Average Depths with One										
			Anisotropic Etch," Research Disclosure, No. 316, Emsworth, GB, August, 1990, pp. 688-								
		689.									
	AO	l l ' '	Zou et al., "Single-Chip Fabrication of Integrated Fluid System (IFS), <i>IEEE Workshop on Micro Electro Mechanical Systems</i> , New York, NY: IEEE, 25 January 1998, pp 448-453								
	AP	"Method of Making Senarate Regions of Various Average Denths with one Anisotropic									
		Etch," Resea	Etch," Research Disclosure, GB, Industrial Opportunities Ltd., Havant, No. 316, August								
			1990 Sugiyama et al., "Micro-Diaphram Pressure Sensor," 1986 IEEE, 8.3, 184-IEDM, pp 184-								
	AQ	187.									
EXAMINE	R				DATE CONSIDERED						
* EXAMIN					nformance with MPEP 609. Draw with next communication to appli		ough ci	tation if not in			